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拓電半導體

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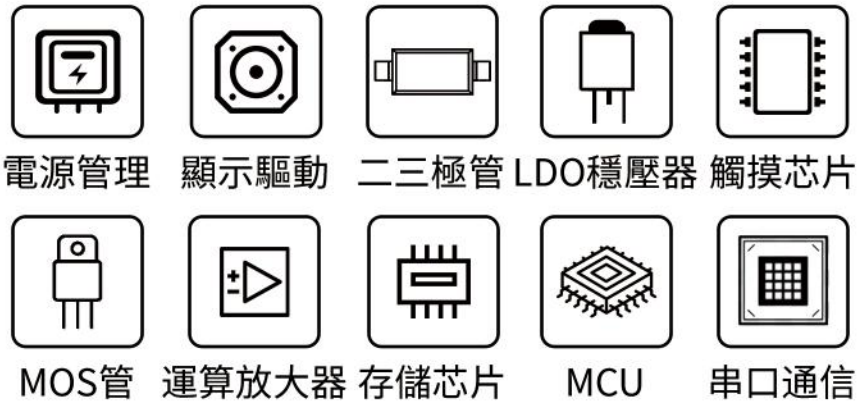


H5VL10B-TD

產品規格說明書

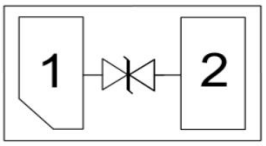
Features

◇ 68W (8/20μs) Peak Pulse Power
◇ Low Capacitance ESD Protection
◇ **DFN1006-2** Package
◇ RoHS Compliant
◇ Matte Tin Lead finish (Pb-Free)
◇ Protect One High Speed Data Line
◇ Meet IEC61000-4-2 Level 4:
Contact Discharge > 25kV
Air Discharge > 25kV

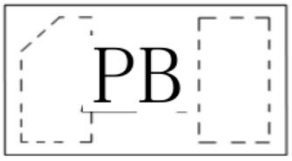
Applications

◇ Communication System
◇ Portable Instrumentation
◇ Audio and Video Equipment
◇ Computers and Peripherals
◇ USB 1.1, USB 1.0 Ports

Circuit Diagram



Package Outline



PB= Device Code

Ordering information

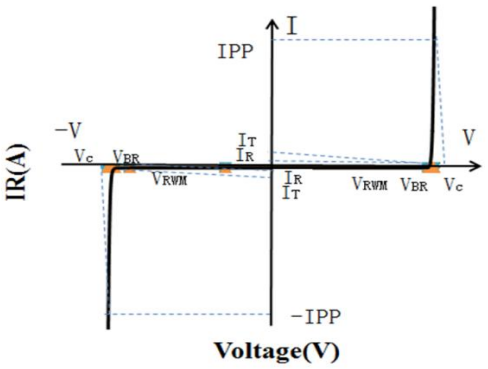
Device	Package	Reel Size	Qty / Reel
H5VL10B-TD	DFN1006-2	7 inch	10000

Maximum Ratings (Ta = 25℃)

Symbol	Parameter	Value	Unit
P_{PK}	Peak Pulse Power	68	W
I_{PP}	Peak Pulse Current	5	A
V_{ESD} (Contact)	Contact ESD Voltage per IEC61000-4-2	30	kV
V_{ESD} (Air)	Air ESD Voltage per IEC61000-4-2	30	kV
TJ	Junction Temperature	-55 to +150	℃
TSTG	Storage Temperature	-55 to +150	℃

Portion Electronics Parameter

Symbol	Parameter
I_T	Test Current
I_{PP}	Maximum Reverse Peak Pulse Current
Vc	Clamping Voltage @Ic



Electrical Characteristics (Ta = 25℃)

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
VRWM	Reverse Working Peak Voltage				5	V
VBR	Reverse Breakdown Voltage	IT = 1mA	5.7		9	V
IR	Reverse Leakage Current	VRWM = 5V			0.1	μA
VC	Clamping Voltage	IPP = 1A (8/20μs)			12	V
VC	Clamping Voltage	IPP = 5A (8/20 μs)			17	V
CJ	Capacitance	VR = 0V, f = 1MHz	8	8.9	15	pF

SURGE CURRENT WAVEFORM:

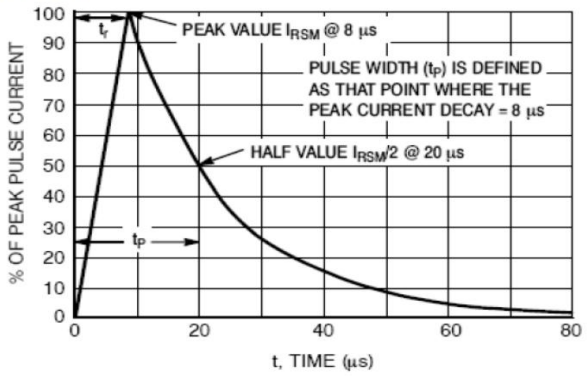


Figure 1. 8 x 20 μs Pulse Waveform

CAPACITANCE CURVE: